# Plastic Darlington Complementary Silicon Power Transistors

Plastic Darlington complementary silicon power transistors are designed for general purpose amplifier and low-speed switching applications.

## **Features**

- ESD Ratings: Machine Model, C; > 400 V Human Body Model, 3B; > 8000 V
- Epoxy Meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant\*

# **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage 2N6034G 2N6035G, 2N6038G 2N6036G, 2N6039G	V <sub>CEO</sub>	40 60 80	Vdc
Collector–Base Voltage 2N6034G 2N6035G, 2N6038G 2N6036G, 2N6039G	V <sub>CBO</sub>	40 60 80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	4.0	Adc
Collector Current – Peak	I <sub>CM</sub>	8.0	Apk
Base Current	I <sub>B</sub>	100	mAdc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	40 320	W mW/°C
Total Device Dissipation  @ T <sub>C</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.12	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	83.3	°C/W

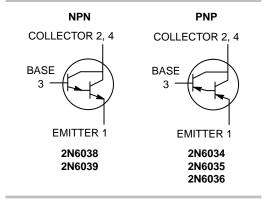
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



# ON Semiconductor®

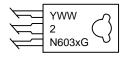
http://onsemi.com

# 4.0 AMPERES DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS 40, 60, 80 VOLTS, 40 WATTS





#### MARKING DIAGRAM



Y = Year WW = Work Week 2N603x = Device Code x = 4, 5, 6, 8, 9 G = Pb-Free Package

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u> </u>			<u> </u>
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0) 2N6034G 2N6035G, 2N6038G 2N6036G, 2N6039G	V <sub>CEO</sub> (sus)	40 60 80	- - -	Vdc
Collector–Cutoff Current (V <sub>CE</sub> = 40 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>		100	μΑ
2N6034G (V <sub>CE</sub> = 60 Vdc, I <sub>B</sub> = 0) 2N6035G, 2N6038G		_	100	
(V <sub>CE</sub> = 80 Vdc, I <sub>B</sub> = 0) 2N6036G, 2N6039G		-	100	
Collector–Cutoff Current (V <sub>CE</sub> = 40 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc) 2N6034G	I <sub>CEX</sub>	-	100	μΑ
(V <sub>CE</sub> = 60 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc) 2N6035G, 2N6038G (V <sub>CE</sub> = 80 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc)		-	100	
2N6036G, 2N6039G (V <sub>CE</sub> = 40 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc, T <sub>C</sub> = 125°C)		-	100	
2N6034G (V <sub>CF</sub> = 60 Vdc, V <sub>RF(off)</sub> = 1.5 Vdc, T <sub>C</sub> = 125°C)		-	500	
2N6035G, 2N6038G (V <sub>CE</sub> = 80 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc, T <sub>C</sub> = 125°C) 2N6036G, 2N6039G		_	500	
Collector–Cutoff Current	I <sub>CBO</sub>		000	mAdc
(V <sub>CB</sub> = 40 Vdc, I <sub>E</sub> = 0) 2N6034G (V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0)		-	0.5	
2N6035G, 2N6038G (V <sub>CB</sub> = 80 Vdc, I <sub>E</sub> = 0)		-	0.5	
2N6036G, 2N6039G  Emitter–Cutoff Current	I <sub>EBO</sub>		0.5	mAdc
$(V_{BE} = 5.0 \text{ Vdc}, I_C = 0)$	·EBO	-	2.0	iiii tao
ON CHARACTERISTICS			1	1
DC Current Gain ( $I_C = 0.5 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}$ ) ( $I_C = 2.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}$ ) ( $I_C = 4.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}$ )	h <sub>FE</sub>	500 750 100	15,000 -	_
Collector–Emitter Saturation Voltage ( $I_C = 2.0$ Adc, $I_B = 8.0$ mAdc) ( $I_C = 4.0$ Adc, $I_B = 40$ mAdc)	V <sub>CE(sat)</sub>	- -	2.0 3.0	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = 4.0 Adc, I <sub>B</sub> = 40 mAdc)	V <sub>BE(sat)</sub>	-	4.0	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 2.0 Adc, V <sub>CE</sub> = 3.0 Vdc)	V <sub>BE(on)</sub>	_	2.8	Vdc
DYNAMIC CHARACTERISTICS	l l		1	<u> </u>
Small–Signal Current–Gain (I <sub>C</sub> = 0.75 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 MHz)	h <sub>fe</sub>	25	-	-
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz) 2N6034G, 2N6035G, 2N6036G	C <sub>ob</sub>	_	200	pF
2N6038G, 2N6039G		-	100	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
\*Indicates JEDEC Registered Data.

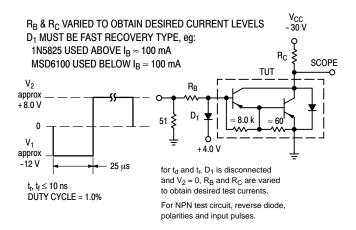


Figure 1. Switching Times Test Circuit

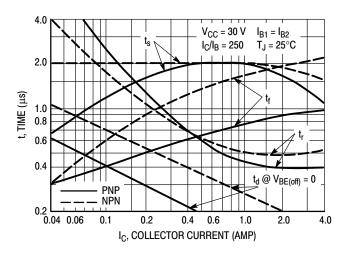


Figure 2. Switching Times

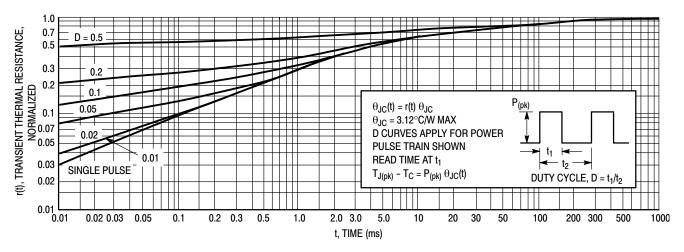
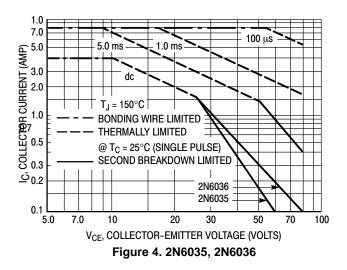


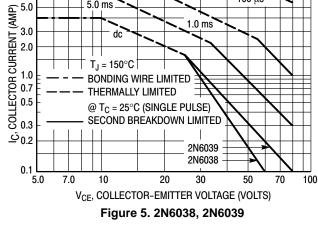
Figure 3. Thermal Response

# **ACTIVE-REGION SAFE-OPERATING AREA**

7.0

5.0 ms



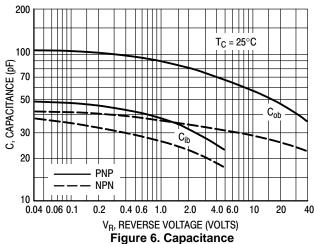


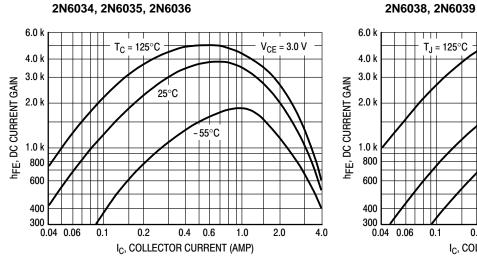
100 μs

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I<sub>C</sub> - V<sub>CE</sub> limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 4 and 5 is based on  $T_{J(pk)} = 150$ °C; T<sub>C</sub> is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided T<sub>J(pk)</sub> < 150 °C.  $T_{J(pk)}$  may be calculated from the data in Figure 3. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

**PNP** 





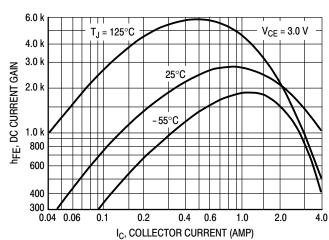


Figure 7. DC Current Gain

**NPN** 

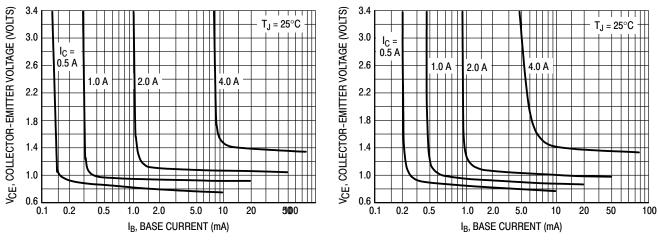


Figure 8. Collector Saturation Region

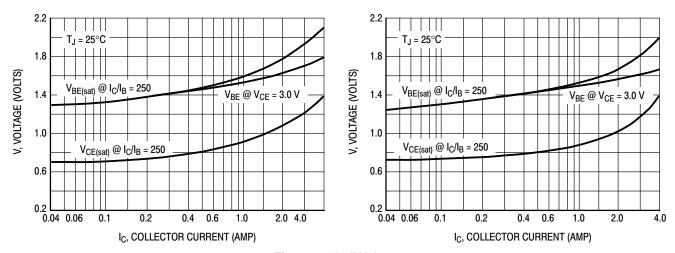
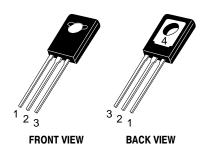


Figure 9. "On" Voltages

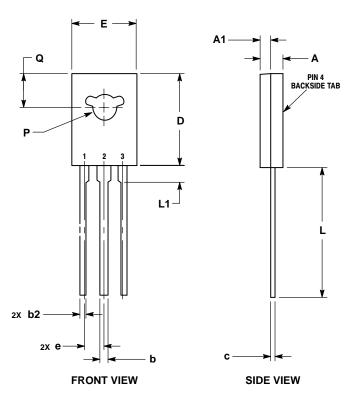
# **ORDERING INFORMATION**

Device	Package	Shipping
2N6034G	TO-225 (Pb-Free)	500 Units / Box
2N6035G	TO-225 (Pb-Free)	500 Units / Box
2N6036G	TO-225 (Pb-Free)	500 Units / Box
2N6038G	TO-225 (Pb-Free)	500 Units / Box
2N6039G	TO-225 (Pb-Free)	500 Units / Box

# PACKAGE DIMENSIONS



TO-225 CASE 77-09 **ISSUE AC** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.40	3.00	
A1	1.00	1.50	
b	0.60	0.90	
b2	0.51	0.88	
С	0.39	0.63	
D	10.60	11.10	
Е	7.40	7.80	
е	2.04	2.54	
L	14.50	16.63	
L1	1.27	2.54	
Р	2.90	3.30	
Q	3.80	4.20	

PIN 1 FMITTER COLLECTOR 2., 4.

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